NINTH BIENNIAL UNIVERSITY/GOVERNMENT/INDUSTRY MICROELECTRONICS SYMPOSIUM

SESSION 1: KEYNOTE SESSION

Thomas Sanders, *General Chairman*
James Freedman, *Technical Program Chairman*

Theme: United States Microelectronics Competitiveness for the 1990's

Guest Speakers:

Dr. Ian Ross, *President*, AT&T Bell Laboratories
Chairman, National Advisory Committee on Semiconductors
Mr. Larry Sumney, *President*, Semiconductor Research Corporation
Dr. John A. White, *Assistant Director for Engineering*, National Science Foundation
Dr. Turner Hasty, *Chief Operating Officer*, SEMATECH
Dr. David Hodges, *Dean*, School of Engineering, University of California, Berkeley, California

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Co-Chairmen: John Blasingame, Tom Wade

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